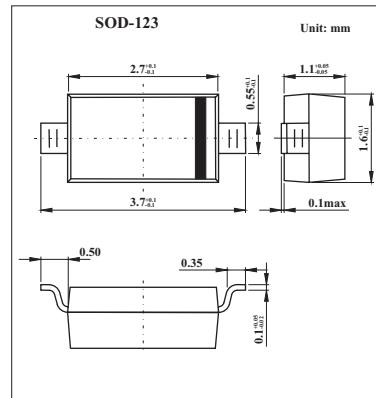


HVR100

■ Features

- High capacitance ratio. ($n = 16.0 \text{ min}$)
- High figure of merit. ($Q = 200 \text{ min}$)
- To be usable at low voltage.
- Small Resin Package (SRP) is suitable for surface mount design.



■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Value	Unit
Reverse Voltage	V_R	15	V
Junction temperature	T_j	125	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +125	$^\circ\text{C}$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Max	Unit
Reverse voltage	V_R	$I_R = 10 \mu\text{A}$	15		V
Reverse current	I_R	$V_R = 9 \text{ V}$		100	nA
Capacitance	C_1	$V_R = 1 \text{ V}, f = 1 \text{ MHz}$	421.5	524.6	pF
	C_3	$V_R = 3 \text{ V}, f = 1 \text{ MHz}$	182	275.7	
	C_5	$V_R = 5 \text{ V}, f = 1 \text{ MHz}$	73.2	121.4	
	C_6	$V_R = 6 \text{ V}, f = 1 \text{ MHz}$	42.2	72.2	
	C_7	$V_R = 7 \text{ V}, f = 1 \text{ MHz}$	26.2	41.6	
	C_8	$V_R = 8 \text{ V}, f = 1 \text{ MHz}$	20.4	28.2	
Capacitance ratio	n	C_1 / C_8	16		
Figure of merit	Q	$C = 450 \text{ pF}, f = 1 \text{ MHz}$	200		
Matching error	$\Delta C/C^{*1}$	$V_R = 1 \text{ to } 8 \text{ V}$		3.0	%
ESD-Capability ^{*1}		$C=200 \text{ pF}$, Both forward and reverse direction 1 pulse.	80		V

Notes

1.Failure criterion ; $I_R \geq 100 \text{nA}$ at $V_R = 9 \text{ V}$

■ Marking

Marking	2
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